

This listing of claims will replace all prior versions, and listings, of claims in the application:

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1 Claim 1 (currently amended): A solid-state imaging device  
2 comprising:  
3 a pixel unit constituted by a two-dimensional array of  
4 pixels for generating charge in correspondence to received  
5 light and accumulating the charge for a predetermined  
6 period of time;  
7 a vertical transfer unit for vertically transferring  
8 charge from the pixels in the pixel unit, a horizontal  
9 transfer unit for horizontally transferring charge from the  
10 vertical transfer unit;  
11 shift gates each provided between each pixel and the  
12 vertical transfer unit for reading out the charge in the  
13 pixels to the vertical transfer unit, gate electrodes for  
14 controlling the shift gates; and  
15 a plurality of lead lines for connecting the gate  
16 electrodes to an external circuit and a plurality of  
17 connection terminals for connecting the gate electrodes to  
18 ~~an~~ the external circuit,  
19 the gate electrodes making up N of gate electrode  
20 groups in which the lines belonging to each coset of  
21 modulo N within successive pixel rows are connected to  
22 common lead lines, N being a predetermined natural number  
23 between 4 and one half the number of pixels in a column,  
24 and also being the minimum number corresponding to the  
25 periodic unit about connections from said gate electrodes  
26 to said connection terminals within said successive pixel  
27 rows, the gate electrodes having common connection  
28 terminals to reduce the number of the connection terminals  
29 to less than N.

1 Claim 2 (currently amended): A solid-state imaging device  
2 comprising:

3 a pixel unit constituted by a two-dimensional array of  
4 pixels for generating charge in correspondence to received  
5 light and accumulating the charge for a predetermined  
6 period of time;

7 a vertical transfer unit for vertically transferring  
8 charge from the pixels in the pixel unit, a horizontal  
9 transfer unit for horizontally transferring charge from the  
10 vertical transfer unit;

11 shift gates each provided between each pixel and the  
12 vertical transfer unit for reading out the charge in the  
13 pixels to the vertical transfer unit, gate electrodes for  
14 controlling the shift gates; and

15 a plurality of lead lines for connecting the gate  
16 electrodes to an external circuit and a plurality of  
17 connection terminals for connecting the gate electrodes to  
18 ~~an~~ the external circuit,

19 gate control lines connected to gate electrode groups  
20 in which horizontal lines belonging to each coset of modulo  
21  $N$  within successive pixel rows are connected commonly,  $N$   
22 being a predetermined natural number between 4 and one half  
23 the number of pixels in a column, and also being the  
24 minimum number corresponding to the periodic unit about  
25 connections from said gate electrodes to said connection  
26 terminals within said successive pixel rows, being combined  
27 with each other so as to reduce the number of the  
28 connection terminals to less than  $N$ .

1 Claim 3 (currently amended): A solid-state imaging device  
2 comprising:

3 a pixel unit constituted by a two-dimensional array of  
4 pixels for generating charge in correspondence to received  
5 light and accumulating the charge for a predetermined  
6 period of time;

7 a vertical transfer unit for vertically transferring  
8 charge from the pixels in the pixel unit, a horizontal  
9 transfer unit for horizontally transferring charge from the  
10 vertical transfer unit;

11 shift gates each provided between each pixel and the  
12 vertical transfer unit for reading out the charge in the  
13 pixels to the vertical transfer unit, gate electrodes for  
14 controlling the shift gates; and

15 a plurality of lead lines for connecting the gate  
16 electrodes to an external circuit and a plurality of  
17 connection terminals for connecting the gate electrodes to  
18 ~~an~~ the external circuit,

19 the gate electrodes being provided in a predetermined  
20 number N of gate electrode groups such that horizontal line  
21 number of the gate electrode groups which are connected to  
22 respective common lead lines belong to each same residue  
23 class of modulo N, N being a predetermined natural number  
24 between 4 and one half the number of pixels in a column,  
25 and also being the minimum number corresponding to the  
26 periodic unit about connections from said gate electrodes  
27 to said connection terminals within said successive pixel  
28 rows, some of the gate electrode groups being commonly  
29 connected so that the connection terminals are less in  
30 number than N.

1 Claim 4 (currently amended): A solid-state imaging device  
2 comprising:

3 a pixel unit constituted by a two-dimensional array of  
4 pixels for generating charge in correspondence to received  
5 light and accumulating the charge for a predetermined  
6 period of time;

7 a vertical transfer unit for vertically transferring  
8 charge from the pixels in the pixel unit, a horizontal  
9 transfer unit for horizontally transferring charge from the  
10 vertical transfer unit;

11 shift gates each provided between each pixel and the  
12 vertical transfer unit for reading out the charge in the  
13 pixels to the vertical transfer unit, gate electrodes for  
14 controlling the shift gates; and

15 a plurality of lead lines for connecting the gate  
16 electrodes to an external circuit and a plurality of  
17 connection terminals for connecting the gate electrodes to  
18 ~~an~~ the external circuit,

19 the gate electrodes making up N of gate electrode  
20 groups in which the lines belonging to each coset of modulo  
21 N within successive pixel rows are connected to common lead  
22 lines, N being a predetermined natural number between 4 and  
23 one half the number of pixels in a column, and also being a  
24 the minimum number corresponding to the periodic unit about  
25 connections from said gate electrodes to said connection  
26 terminals within said successive pixel rows, the gate  
27 electrode groups having common connections to reduce the  
28 number of the connection terminals to less than N,

29 wherein the commonly connected gate electrode groups  
30 are always controlled in the same way in each of all  
31 predetermined read-out modes including selective pixel  
32 read-out modes by selective shift gate driving.

1 Claim 5 (currently amended): A solid-state imaging device  
2 comprising:  
3 a pixel unit constituted by a two-dimensional array of  
4 pixels for generating charge in correspondence to received  
5 light and accumulating the charge for a predetermined  
6 period of time;  
7 a vertical transfer unit for vertically transferring  
8 charge from the pixels in the pixel unit, a horizontal  
9 transfer unit for horizontally transferring charge from the  
10 vertical transfer unit;  
11 shift gates each provided between each pixel and the  
12 vertical transfer unit for reading out the charge in the  
13 pixels to the vertical transfer unit, gate electrodes for  
14 controlling the shift gates; and  
15 a plurality of lead lines for connecting the gate  
16 electrodes to an external circuit and a plurality of  
17 connection terminals for connecting the gate electrodes to  
18 ~~an~~ the external circuit,  
19 gate control lines connected to gate electrode groups  
20 in which the horizontal lines belonging to each coset of  
21 modulo N within successive pixel rows are connected  
22 commonly, N being a predetermined natural number between 4  
23 and one half the number of pixels in a column, and also  
24 being the minimum number corresponding to the periodic unit  
25 about connections from said gate electrodes to said  
26 connection terminals within said successive pixel rows,  
27 being combined with each other so as to reduce the number  
28 of the connection terminals to less than N,  
29 wherein the commonly connected gate electrode groups  
30 are always controlled in the same way in each of all  
31 predetermined read-out modes including selective pixel  
32 read-out modes by selective shift gate driving.

1 Claim 6 (currently amended): A solid-state imaging device  
2 comprising:  
3 a pixel unit constituted by a two-dimensional array of  
4 pixels for generating charge in correspondence to received  
5 light and accumulating the charge for a predetermined  
6 period of time;  
7 a vertical transfer unit for vertically transferring  
8 charge from the pixels in the pixel unit, a horizontal  
9 transfer unit for horizontally transferring charge from the  
10 vertical transfer unit;  
11 shift gates each provided between each pixel and the  
12 vertical transfer unit for reading out the charge in the  
13 pixels to the vertical transfer unit, gate electrodes for  
14 controlling the shift gates; and  
15 a plurality of lead lines for connecting the gate  
16 electrodes to an external circuit and a plurality of  
17 connection terminals for connecting the gate electrodes to  
18 ~~an~~ the external circuit,  
19 the gate electrodes being provided in a predetermined  
20 number N of gate electrode groups such that horizontal line  
21 number of the gate electrode groups which are connected to  
22 respective common lead lines belong to each same residue  
23 class of modulo N, N being a predetermined natural number  
24 between 4 and one half the number of pixels in a column,  
25 and also being the minimum number corresponding to the  
26 periodic unit about connections from said gate electrodes  
27 to said connection terminals within said successive pixel  
28 rows, some of the gate electrode groups being commonly  
29 connected so that the connection terminals are less in  
30 number than N,

31 wherein the commonly connected gate electrode groups  
32 are always controlled in the same way in each of all  
33 predetermined read-out modes including selective pixel  
34 read-out modes by selective shift gate driving.

1 Claim 7 (previously presented): The solid-state imaging  
2 device according to claim 4, wherein gate electrode groups  
3 controlled in each of all the predetermined read-out modes  
4 are set such as to provide a minimum number of connection  
5 terminals for connecting the gate electrodes to an external  
6 circuit.

1 Claim 8 (previously presented): The solid-state imaging  
2 device according to claim 5 wherein gate electrode groups  
3 controlled in each of all the predetermined read-out modes  
4 are set such as to provide a minimum number of connection  
5 terminals for connecting the gate electrodes to an external  
6 circuit.

1 Claim 9 (previously presented): The solid-state imaging  
2 device according to claim 6 wherein gate electrode groups  
3 controlled in each of all the predetermined read-out modes  
4 are set such as to provide a minimum number of connection  
5 terminals for connecting the gate electrodes to an external  
6 circuit.

Claims 10 and 11 (canceled)

1 Claim 12 (previously presented): The solid-state imaging  
2 device of claim 1 wherein at least two horizontal lines  
3 belonging to the same pixel group but to different gate

4 electrode groups are connected to a common connection  
5 terminal.

1 Claim 13 (previously presented): The solid-state imaging  
2 device of claim 2 wherein at least two horizontal lines  
3 belonging to the same pixel group but to different gate  
4 electrode groups are connected to a common connection  
5 terminal.

1 Claim 14 (previously presented): The solid-state imaging  
2 device of claim 3 wherein at least two horizontal lines  
3 belonging to the same pixel group but to different gate  
4 electrode groups are connected to a common connection  
5 terminal.

6 1 Claim 15 (previously presented): The solid-state imaging  
2 device of claim 4 wherein at least two horizontal lines  
3 belonging to the same pixel group but to different gate  
4 electrode groups are connected to a common connection  
5 terminal.

1 Claim 16 (previously presented): The solid-state imaging  
2 device of claim 5 wherein at least two horizontal lines  
3 belonging to the same pixel group but to different gate  
4 electrode groups are connected to a common connection  
5 terminal.

1 Claim 17 (previously presented): The solid-state imaging  
2 device of claim 6 wherein at least two horizontal lines  
3 belonging to the same pixel group but to different gate  
4 electrode groups are connected to a common connection  
5 terminal.



1 Claim 18 (previously presented): The solid-state imaging  
2 device of claim 1 wherein only two connection terminals  
3 connected to said vertical transfer unit are not connected  
4 to any of the gate electrodes.

1 Claim 19 (previously presented): The solid-state imaging  
2 device of claim 2 wherein only two connection terminals  
3 connected to said vertical transfer unit are not connected  
4 to any of the gate electrodes.

1 Claim 20 (previously presented): The solid-state imaging  
2 device of claim 3 wherein only two connection terminals  
3 connected to said vertical transfer unit are not connected  
4 to any of the gate electrodes.

61  
1 Claim 21 (previously presented): The solid-state imaging  
2 device of claim 4 wherein only two connection terminals  
3 connected to said vertical transfer unit are not connected  
4 to any of the gate electrodes.

1 Claim 22 (previously presented): The solid-state imaging  
2 device of claim 5 wherein only two connection terminals  
3 connected to said vertical transfer unit are not connected  
4 to any of the gate electrodes.

1 Claim 23 (previously presented): The solid-state imaging  
2 device of claim 6 wherein only two connection terminals  
3 connected to said vertical transfer unit are not connected  
4 to any of the gate electrodes.

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